1. General description

NPN high-voltage low V_{CEsat} transistor in a SOT89 (SC-62) medium power and flat lead Surface-Mounted Device (SMD) plastic package.

PNP complement: PBHV9115X-Q

2. Features and benefits

- High voltage
- Low collector-emitter saturation voltage V_{CEsat}
- High collector current capability I_C and I_{CM}
- High collector current gain (h_{FE}) at high I_C
- Medium power SMD plastic package
- Qualified according to AEC-Q101 and recommended for use in automotive applications

3. Applications

- LED driver for LED chain module
- LCD backlighting
- · High Intensity Discharge (HID) front lighting
- Automotive motor management
- · Hook switch for wired telecom
- Switch Mode Power Supply (SMPS)

4. Quick reference data

Table 1. Quick reference data

| and the special control of the special contro | | | | | | | |
|--|---------------------------|---|--|-----|-----|-----|------|
| Symbol | Parameter | Conditions | | Min | Тур | Max | Unit |
| V _{CEO} | collector-emitter voltage | open base | | - | - | 150 | V |
| I _C | collector current | | | - | - | 1 | Α |
| h _{FE} | DC current gain | V_{CE} = 10 V; I_{C} = 50 mA; T_{amb} = 25 °C | | 100 | 250 | - | |



150 V, 1 A NPN high-voltage low VCEsat transistor

5. Pinning information

Table 2. Pinning information

| Pin | Symbol | Description | Simplified outline | Graphic symbol |
|-----|--------|-------------|--------------------|---------------------------------------|
| 1 | Е | emitter | | С |
| 2 | С | collector | | , , , , , , , , , , , , , , , , , , , |
| 3 | В | base | 3 2 1 SOT89 | B — E sym042 |

6. Ordering information

Table 3. Ordering information

| Type number | Package | | | | | |
|-------------|---------|--|---------|--|--|--|
| | Name | Description | Version | | | |
| PBHV8115X-Q | SOT89 | plastic, surface-mounted package; 3 leads; 1.5 mm pitch; 4.5 mm x 2.5 mm x 1.5 mm body | SOT89 | | | |

7. Marking

Table 4. Marking codes

| Type number | Marking code[1] |
|-------------|-----------------|
| PBHV8115X-Q | %4F |

[1] % = placeholder for manufacturing site code

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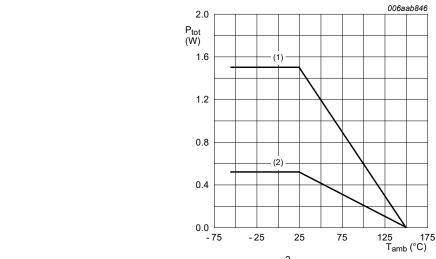
8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

| Symbol | Parameter | Conditions | | Min | Max | Unit |
|------------------|---------------------------|-------------------------------------|-----|-----|------|------|
| V _{CBO} | collector-base voltage | open emitter | | - | 400 | V |
| V _{CEO} | collector-emitter voltage | open base | | - | 150 | V |
| V _{EBO} | emitter-base voltage | open collector | | - | 6 | V |
| I _C | collector current | | | - | 1 | Α |
| I _{CM} | peak collector current | single pulse; t _p ≤ 1 ms | | - | 2 | Α |
| I _{BM} | peak base current | | | - | 400 | mA |
| P _{tot} | total power dissipation | T _{amb} ≤ 25 °C | [1] | - | 0.52 | W |
| | | | [2] | - | 1.5 | W |
| Tj | junction temperature | | | - | 150 | °C |
| T _{amb} | ambient temperature | | | -55 | 150 | °C |
| T _{stg} | storage temperature | | | -65 | 150 | °C |

- Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint. Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 6 cm².



- (1) FR4 PCB, mounting pad for collector 6 cm²
- (2) FR4 PCB, standard footprint

Power derating curves

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9. Thermal characteristics

Table 6. Thermal characteristics

| Symbol | Parameter | Conditions | | Min | Тур | Max | Unit |
|-----------------------|--|-------------|-----|-----|-----|-----|------|
| R _{th(j-a)} | thermal resistance from | in free air | [1] | - | - | 240 | K/W |
| juno | unction to ambient | | [2] | - | - | 83 | K/W |
| R _{th(j-sp)} | thermal resistance from junction to solder point | | | - | - | 20 | K/W |

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 6 cm².

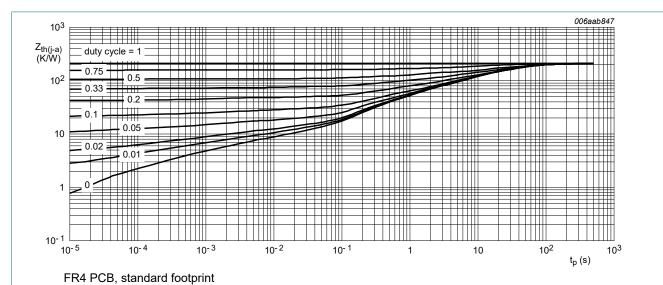


Fig. 2. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

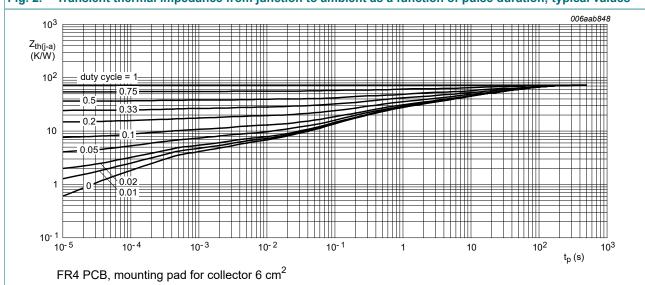


Fig. 3. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

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10. Characteristics

Table 7. Characteristics

| Symbol | Parameter | Conditions | Min | Тур | Max | Unit |
|--------------------|-----------------------------------|---|-----|------|-----|------|
| I _{CBO} | collector-base cut-off | V _{CB} = 120 V; I _E = 0 A; T _{amb} = 25 °C | - | - | 100 | nA |
| | current | V _{CB} = 120 V; I _E = 0 A; T _j = 150 °C | - | - | 10 | μΑ |
| I _{EBO} | emitter-base cut-off current | V _{EB} = 4 V; I _C = 0 A; T _{amb} = 25 °C | - | - | 100 | nA |
| I _{CES} | collector-emitter cut-off current | $V_{CE} = 120 \text{ V}; V_{BE} = 0 \text{ V}; T_{amb} = 25 \text{ °C}$ | - | - | 100 | nA |
| h _{FE} | DC current gain | V _{CE} = 10 V; I _C = 50 mA; T _{amb} = 25 °C | 100 | 250 | - | |
| | | V_{CE} = 10 V; I_{C} = 100 mA; pulsed; t_{p} ≤ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C | 100 | 250 | - | |
| | | V_{CE} = 10 V; I_{C} = 0.5 A; pulsed; t_{p} ≤ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C | 50 | 160 | - | |
| | | V_{CE} = 10 V; I_{C} = 1 A; t_{p} ≤ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C | 10 | 30 | - | |
| V _{CEsat} | collector-emitter | I _C = 100 mA; I _B = 20 mA; T _{amb} = 25 °C | - | 33 | 50 | mV |
| | saturation voltage | I _C = 100 mA; I _B = 10 mA; T _{amb} = 25 °C | - | 40 | 60 | mV |
| | | I_C = 1 A; I_B = 0.2 A; pulsed; $t_p \le 300 \ \mu s$; δ ≤ 0.02; T_{amb} = 25 °C | - | 225 | 350 | mV |
| V _{BEsat} | base-emitter saturation voltage | I_C = 1 A; I_B = 200 mA; pulsed; t_p ≤ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C | - | 1.1 | 1.2 | V |
| t _d | delay time | V _{CC} = 6 V; I _C = 0.5 A; I _{Bon} = 0.1 A; | - | 7 | - | ns |
| t _r | rise time | I _{Boff} = -0.1 A; T _{amb} = 25 °C | - | 565 | - | ns |
| t _{on} | turn-on time | | - | 572 | - | ns |
| t _s | storage time | | - | 1530 | - | ns |
| t _f | fall time | | - | 700 | - | ns |
| t _{off} | turn-off time | | - | 2230 | - | ns |
| f _T | transition frequency | V_{CE} = 10 V; I_{C} = 10 mA; f = 100 MHz; T_{amb} = 25 °C | - | 30 | - | MHz |
| C _c | collector capacitance | $V_{CB} = 20 \text{ V}; I_E = 0 \text{ A}; i_e = 0 \text{ A}; f = 1 \text{ MHz}; $ $T_{amb} = 25 ^{\circ}\text{C}$ | - | 5.7 | - | pF |
| C _e | emitter capacitance | $V_{EB} = 0.5 \text{ V}; I_{C} = 0 \text{ A}; i_{c} = 0 \text{ A};$ $f = 1 \text{ MHz}; T_{amb} = 25 ^{\circ}\text{C}$ | - | 150 | - | pF |

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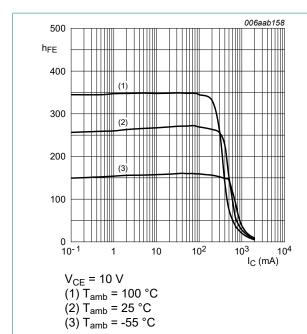


Fig. 4. DC current gain as a function of collector current; typical values

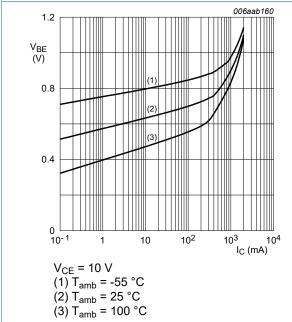


Fig. 6. Base-emitter voltage as a function of collector current; typical values

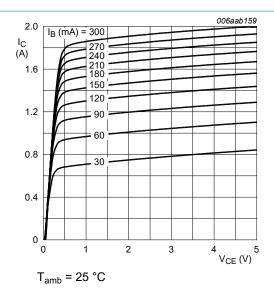
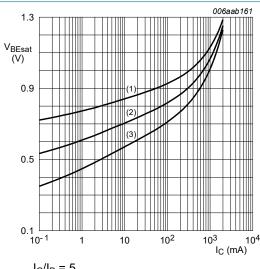


Fig. 5. Collector current as a function of collectoremitter voltage; typical values



 $I_{\rm C}/I_{\rm B} = 5$ (1) $T_{\rm amb} = -55~{\rm ^{\circ}C}$ (2) $T_{\rm amb} = 25~{\rm ^{\circ}C}$ (3) $T_{\rm amb} = 100~{\rm ^{\circ}C}$

Fig. 7. Base-emitter saturation voltage as a function of collector current; typical values

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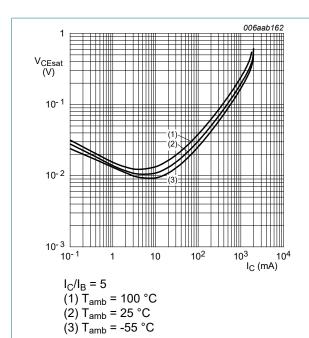


Fig. 8. Collector-emitter saturation voltage as a function of collector current; typical values

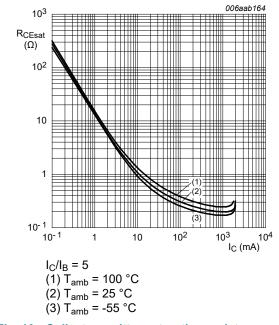


Fig. 10. Collector-emitter saturation resistance as a function of collector current; typical values

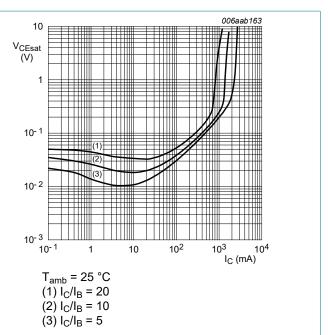


Fig. 9. Collector-emitter saturation voltage as a function of collector current; typical values

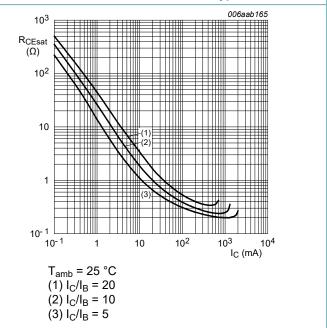
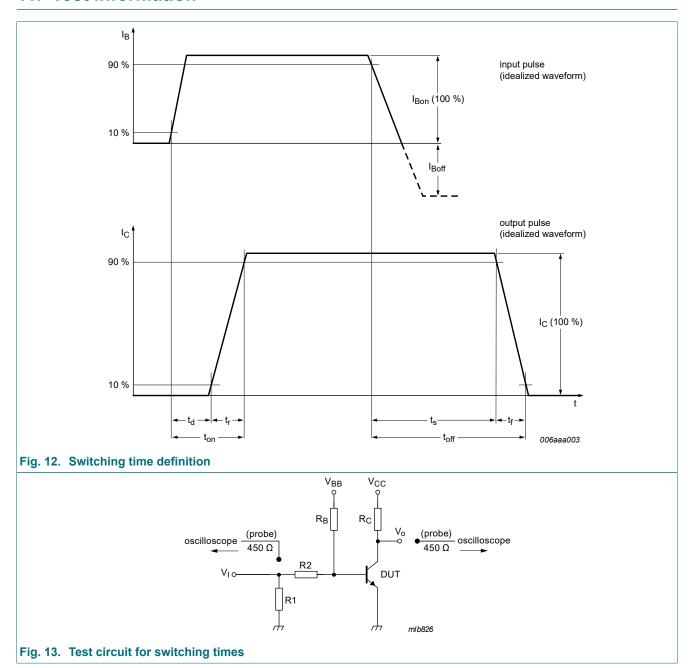


Fig. 11. Collector-emitter saturation resistance as a function of collector current; typical values

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11. Test information

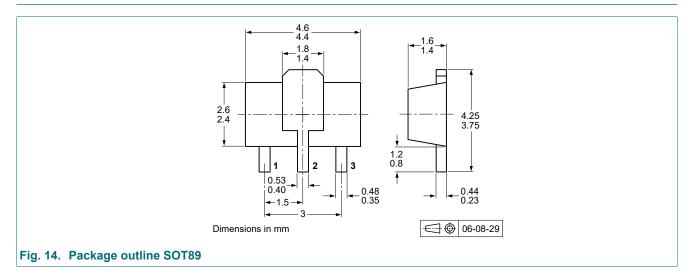


Quality information

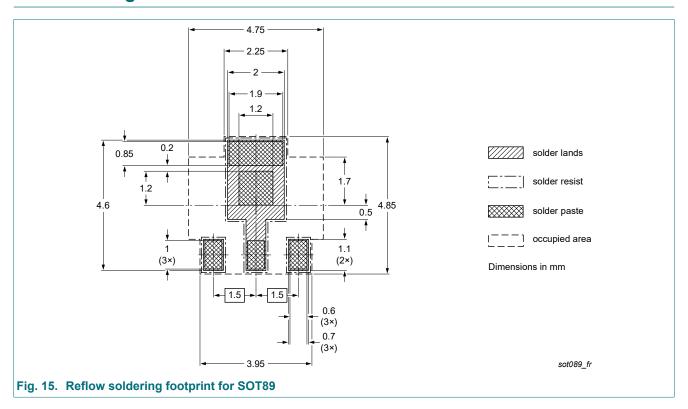
This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101 - Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

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12. Package outline

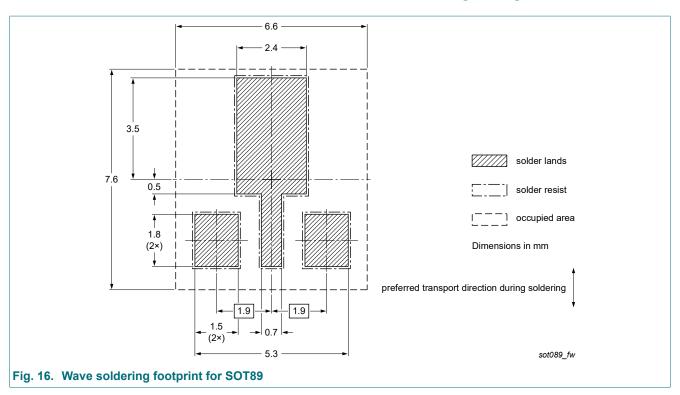


13. Soldering



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14. Revision history

Table 8. Revision history

| Data sheet ID | Release date | Data sheet status | Change notice | Supersedes |
|-----------------|--------------|--------------------|---------------|------------|
| PBHV8115X-Q v.1 | 20231004 | Product data sheet | - | - |

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15. Legal information

Data sheet status

| Document status [1][2] | Product status [3] | Definition |
|--------------------------------|-----------------------|---|
| Objective [short] data sheet | Development | This document contains data from the objective specification for product development. |
| Preliminary [short] data sheet | Qualification | This document contains data from the preliminary specification. |
| Product [short] data sheet | Production | This document contains the product specification. |

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